

n-channel JFET designed for . . .



Performance Curves NRL
See Section 4

- **VHF/UHF Amplifiers**
- **Mixers**
- **Oscillators**

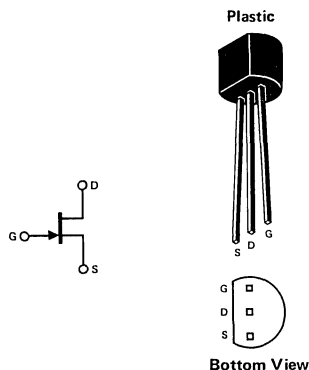
BENEFITS

- Low Cost
- Automatic Insertion Package

ABSOLUTE MAXIMUM RATINGS (25°C)

Drain-Gate Voltage 25 V
 Source-Gate Voltage 25 V
 Drain-Source Voltage 25 V
 Forward Gate Current 10 mA
 Total Device Dissipation at 25°C Ambient
 (Derate 3.27 mW/°C) 360 mW
 Operating Temperature Range -55 to 135°C
 Storage Temperature Range -55 to 150°C
 Lead Temperature Range
 (1/16" from case for 10 seconds) 300°C

TO-92
See Section 6



ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic			Min	Typ	Max	Unit	Test Conditions	
1	S T A T I C	I _{GSS} Gate Reverse Current		−0.01	−100	nA	V _{GS} = −10 V, V _{DS} = 0	
2		BV _{GSS} Gate-Source Breakdown Voltage	−25			V	I _G = −10 μA, V _{DS} = 0	
3		V _{GS(off)} Gate-Source Cutoff Voltage	−0.5		−10.0		V _{DS} = 10 V, I _D = 1 μA	
4		I _{DSS} Saturation Drain Current	1		25	mA	V _{DS} = 10 V, V _{GS} = 0, (Note 1)	
5	D Y N	g _{fs} Common-Source Forward Transconductance	1000		7500	μmho	V _{DS} = 10 V, V _{GS} = 0	f = 1 kHz
6		Re(y _{fs}) Common-Source Forward Transconductance	800					f = 100 MHz
7		C _{iss} Common-Source Input Capacitance		3.5		pF		f = 1 MHz
8		C _{rss} Common-Source Reverse Transfer Capacitance		0.85				

NOTE:

1. Pulse test PW = 300 μs , duty cycle $\leq 3\%$.

NRL